

International
IOR Rectifier

11DQ09
11DQ10

SCHOTTKY RECTIFIER

1.1 Amp

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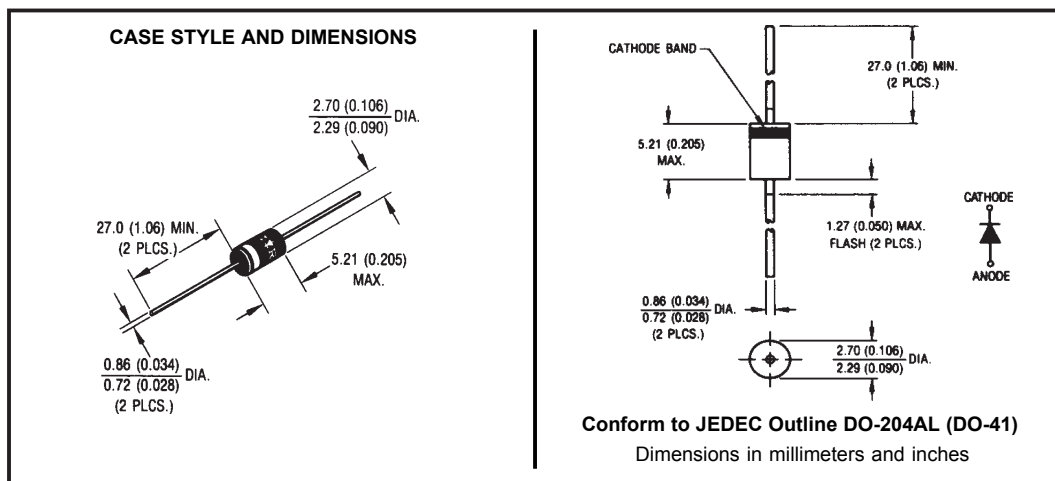
Major Ratings and Characteristics

Characteristics	11DQ..	Units
$I_{F(AV)}$ Rectangular waveform	1.1	A
V_{RRM}	90 / 100	V
I_{FSM} @tp = 5 μ s sine	85	A
V_F @1 Apk, $T_J = 25^\circ\text{C}$	0.85	V
T_J range	-40 to 150	$^\circ\text{C}$

Description/ Features

The 11DQ.. axial leaded Schottky rectifier has been optimized for very low forward voltage drop, with moderate leakage. Typical applications are in switching power supplies, converters, free-wheeling diodes, and reverse battery protection.

- Low profile, axial leaded outline
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Very low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability



Voltage Ratings

Part number	11DQ09	11DQ10
V_R Max. DC Reverse Voltage (V)	90	100
V_{RWM} Max. Working Peak Reverse Voltage (V)		

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Absolute Maximum Ratings

Parameters	11DQ..	Units	Conditions
$I_{F(AV)}$ Max. Average Forward Current * See Fig. 4	1.1	A	50% duty cycle @ $T_C = 75^\circ\text{C}$, rectangular wave form
I_{FSM} Max. Peak One Cycle Non-Repetitive Surge Current * See Fig. 6	85	A	5 μs Sine or 3 μs Rect. pulse
	14		10ms Sine or 6ms Rect. pulse
E_{AS} Non-Repetitive Avalanche Energy	1.0	mJ	$T_J = 25^\circ\text{C}$, $I_{AS} = 0.5\text{ Amps}$, $L = 8\text{ mH}$
I_{AR} Repetitive Avalanche Current	0.5	A	Current decaying linearly to zero in 1 μsec Frequency limited by T_J max. $V_A = 1.5 \times V_R$ typical

Electrical Specifications

Parameters	11DQ..	Units	Conditions
V_{FM} Max. Forward Voltage Drop * See Fig. 1 (1)	0.85	V	@ 1A
	0.96	V	@ 2A
	0.68	V	@ 1A
	0.78	V	@ 2A
I_{RM} Max. Reverse Leakage Current * See Fig. 2 (1)	0.5	mA	$T_J = 25^\circ\text{C}$
	1.0	mA	$T_J = 125^\circ\text{C}$
C_T Typical Junction Capacitance	35	pF	$V_R = 5V_{DC}$ (test signal range 100Khz to 1Mhz) 25°C
L_S Typical Series Inductance	8.0	nH	Measured lead to lead 5mm from package body
dv/dt Max. Voltage Rate of Change	10000	V/ μs	(Rated V_R)

(1) Pulse Width < 300 μs , Duty Cycle <2%

Thermal-Mechanical Specifications

Parameters	11DQ..	Units	Conditions
T_J Max. Junction Temperature Range (*)	-40 to 150	$^\circ\text{C}$	
T_{stg} Max. Storage Temperature Range	-40 to 150	$^\circ\text{C}$	
R_{thJA} Max. Thermal Resistance Junction to Ambient	100	$^\circ\text{C/W}$	DC operation Without cooling fin
R_{thJL} Typical Thermal Resistance Junction to Lead	81	$^\circ\text{C/W}$	DC operation (See Fig. 4)
wt Approximate Weight	0.33(0.012)	g (oz.)	
Case Style	DO-204AL(DO-41)		

(*) $\frac{dP_{tot}}{dT_J} < \frac{1}{R_{th(j-a)}}$ thermal runaway condition for a diode on its own heatsink

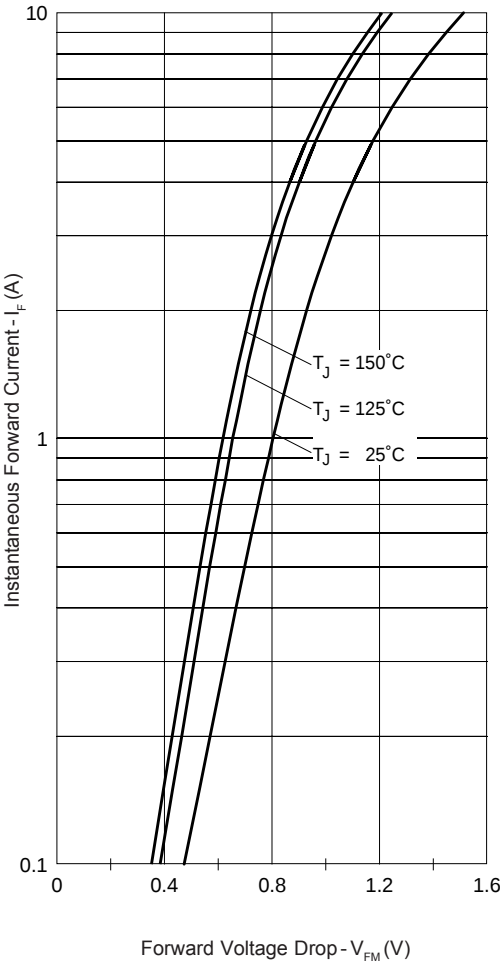


Fig. 1 - Max. Forward Voltage Drop Characteristics

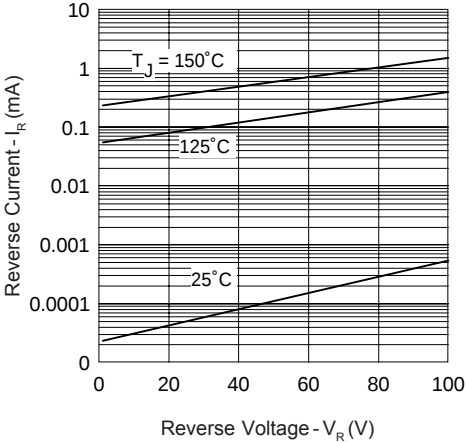


Fig. 2 - Typical Values Of Reverse Current Vs. Reverse Voltage

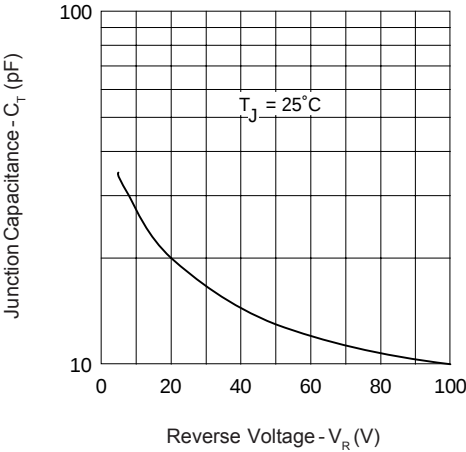


Fig. 3 - Typical Junction Capacitance Vs. Reverse Voltage

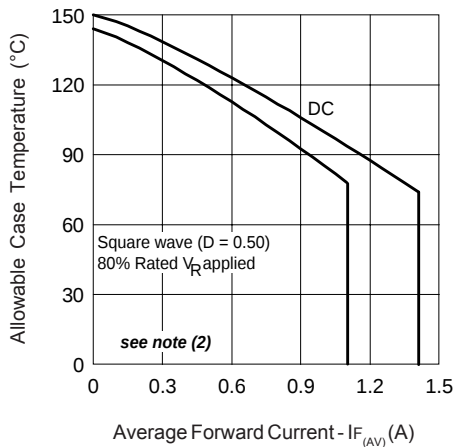


Fig. 4 - Max. Allowable Case Temperature Vs. Average Forward Current

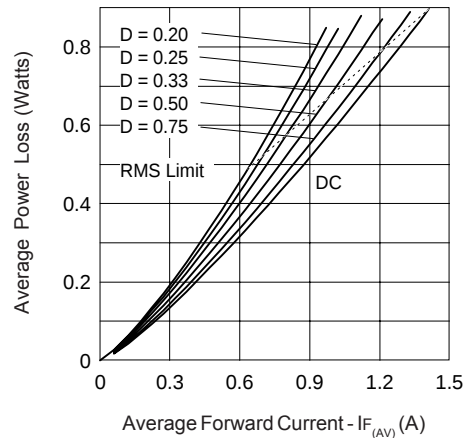


Fig. 5 - Forward Power Loss Characteristics

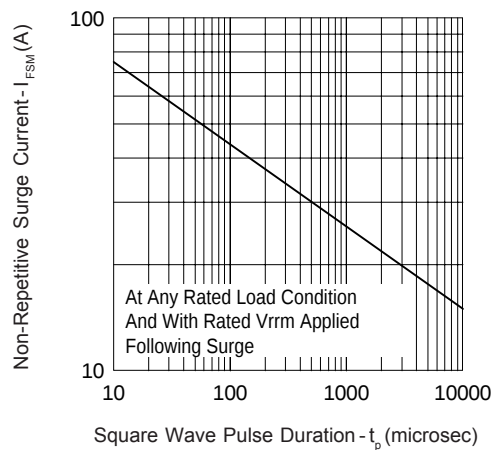


Fig. 6 - Max. Non-Repetitive Surge Current

(2) Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$

Pd = Forward Power Loss = $I_{F(AV)} \times V_{FM} @ (I_{F(AV)} / D)$ (see Fig. 6);

Pd_{REV} = Inverse Power Loss = $V_{R1} \times I_{R1} (1 - D)$; $I_{R1} @ V_{R1} = 80\%$ rated V_R

Ordering Information Table

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Device Code	11	D	Q	10	TR
	1	2	3	4	5
1	-	11 = 1.1A (Axial and small packages - Current is x10)			
2	-	D = DO-41 package			
3	-	Q = Schottky Q.. Series			
4	-	10 = Voltage Ratings			
5	-	TR= Tape & Reel package (5000 pcs)			
	-	= Box package (1000 pcs)			

10 = 100V
09 = 90V

Data and specifications subject to change without notice.
This product has been designed and qualified for Industrial Level.
Qualification Standards can be found on IR's Web site.